

# Tadas Malinauskas

## List of Publications by Year in descending order

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57  
papers

759  
citations

567144

15  
h-index

552653

26  
g-index

57  
all docs

57  
docs citations

57  
times ranked

954  
citing authors

#	ARTICLE	IF	CITATIONS
1	Recombination of free and bound excitons in GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 1723-1740.	0.7	100
2	Determination of free carrier bipolar diffusion coefficient and surface recombination velocity of undoped GaN epilayers. <i>Applied Physics Letters</i> , 2003, 83, 1157-1159.	1.5	68
3	Optical evaluation of carrier lifetime and diffusion length in synthetic diamonds. <i>Diamond and Related Materials</i> , 2008, 17, 1212-1215.	1.8	44
4	Optical monitoring of nonequilibrium carrier lifetime in freestanding GaN by time-resolved four-wave mixing and photoluminescence techniques. <i>Applied Physics Letters</i> , 2006, 88, 202109.	1.5	40
5	Solar water splitting: Efficiency discussion. <i>International Journal of Hydrogen Energy</i> , 2016, 41, 11941-11948.	3.8	37
6	Contribution of dislocations to carrier recombination and transport in highly excited ELO and HVPE GaN layers. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1426-1430.	0.7	32
7	All-optical characterization of carrier lifetimes and diffusion lengths in MOCVD-, ELO-, and HVPE-grown GaN. <i>Journal of Crystal Growth</i> , 2007, 300, 223-227.	0.7	31
8	The determination of high-density carrier plasma parameters in epitaxial layers, semi-insulating and heavily doped crystals of 4H-SiC by a picosecond four-wave mixing technique. <i>Semiconductor Science and Technology</i> , 2006, 21, 952-958.	1.0	29
9	Remote epitaxy of GaN via graphene on GaN/sapphire templates. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 205103.	1.3	26
10	Engineering of InN epilayers by repeated deposition of ultrathin layers in pulsed MOCVD growth. <i>Applied Surface Science</i> , 2018, 427, 1027-1032.	3.1	25
11	In <sub>x</sub> Ga <sub>1-x</sub> N performance as a band-gap-tunable photo-electrode in acidic and basic solutions. <i>Solar Energy Materials and Solar Cells</i> , 2014, 130, 36-41.	3.0	24
12	Optical and structural properties of B <sub>0.05</sub> GaN layers grown on different substrates. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 465307.	1.3	24
13	Diffusion and recombination of degenerate carrier plasma in GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S743-S746.	0.8	19
14	Growth of InN and In-Rich InGa <sub>N</sub> Layers on GaN Templates by Pulsed Metalorganic Chemical Vapor Deposition. <i>Journal of Electronic Materials</i> , 2015, 44, 188-193.	1.0	16
15	Growth of B <sub>0.05</sub> GaN epitaxial layers using close-coupled showerhead MOCVD. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 1138-1141.	0.7	16
16	Carrier dynamics in coalescence overgrowth of GaN nanocolumns. <i>Thin Solid Films</i> , 2010, 519, 863-867.	0.8	15
17	Dynamics of free carrier absorption in InN layers. <i>Applied Physics Letters</i> , 2009, 95, .	1.5	11
18	Layer thickness dependent carrier recombination rate in HVPE GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1703-1706.	0.7	11

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19	Carrier dynamics in blue and green emitting InGaN MQWs. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 977-982.	0.7	11
20	Direct-indirect GeSn band structure formation by laser Radiation: The enhancement of Sn solubility in Ge. <i>Optics and Laser Technology</i> , 2020, 128, 106200.	2.2	11
21	A systematic study of light extraction efficiency enhancement depended on sapphire flipside surface patterning by femtosecond laser. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 285104.	1.3	10
22	Extension of spectral sensitivity of GeSn IR photodiode after laser annealing. <i>Applied Surface Science</i> , 2021, 555, 149711.	3.1	10
23	MOVPE Growth of GaN via Graphene Layers on GaN/Sapphire Templates. <i>Nanomaterials</i> , 2022, 12, 785.	1.9	10
24	Suppression of surface recombination in surface plasmon coupling with an InGaN/GaN multiple quantum well sample. <i>Optics Express</i> , 2011, 19, 18893.	1.7	9
25	Impact of Diffusivity to Carrier Recombination Rate in Nitride Semiconductors: From Bulk GaN to (In,Ga)N Quantum Wells. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JK01.	0.8	9
26	A comparative study on atomic layer deposited oxide film morphology and their electrical breakdown. <i>Surface and Coatings Technology</i> , 2020, 399, 126123.	2.2	8
27	Application of picosecond four-wave mixing and photoluminescence techniques for investigation of carrier dynamics in bulk crystals and heterostructures of GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 1006-1009.	0.8	7
28	Influence of metalorganic precursors flow interruption timing on green InGaN multiple quantum wells. <i>Journal Physics D: Applied Physics</i> , 2016, 49, 505101.	1.3	7
29	Temperature dependent carrier lifetime, diffusion coefficient, and diffusion length in Ge <sub>0.95</sub> Sn <sub>0.05</sub> epilayer. <i>Journal of Applied Physics</i> , 2020, 128, .	1.1	7
30	Nonlinear carrier recombination and transport features in highly excited InN layer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S735-S738.	0.8	6
31	Carrier dynamics in InGaN/GaN multiple quantum wells based on different polishing processes of sapphire substrate. <i>Thin Solid Films</i> , 2010, 518, 7291-7294.	0.8	6
32	Direct study of nonlinear carrier recombination in InGaN quantum well structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2381-2383.	0.8	6
33	Carrier Diffusivity in Highly Excited Bulk SiC, GaN, and Diamond Crystals by Optical Probes. <i>Materials Science Forum</i> , 0, 717-720, 309-312.	0.3	6
34	Significant Carrier Extraction Enhancement at the Interface of an InN/p-GaN Heterojunction under Reverse Bias Voltage. <i>Nanomaterials</i> , 2018, 8, 1039.	1.9	6
35	The detrimental effect of AlGaIn barrier quality on carrier dynamics in AlGaIn/GaN interface. <i>Scientific Reports</i> , 2019, 9, 17346.	1.6	6
36	Hierarchical Carbon Nanocone-Silica Metamaterials: Implications for White Light Photoluminescence. <i>ACS Applied Nano Materials</i> , 2022, 5, 4787-4800.	2.4	6

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37	Holographic study of ultrafast optical excitation in GaN film induced by nonlinear propagation of light. <i>Optics Letters</i> , 2012, 37, 4916.	1.7	5
38	Study of recombination characteristics in MOCVD grown GaN epi-layers on Si. <i>Semiconductor Science and Technology</i> , 2017, 32, 125014.	1.0	5
39	Study of carrier recombination transient characteristics in MOCVD grown GaN dependent on layer thickness. <i>AIP Advances</i> , 2013, 3, 112128.	0.6	4
40	Growth conditions of semi and non-polar GaN on Si with Er <sub>2</sub> O <sub>3</sub> buffer layer. <i>Journal of Alloys and Compounds</i> , 2017, 725, 739-743.	2.8	4
41	Study of the electrical characteristics of CdZnTe Schottky diodes. <i>Materials Science in Semiconductor Processing</i> , 2020, 105, 104705.	1.9	4
42	Studies of carrier dynamics in epitaxial heterostructures by nonlinear optical and microwave techniques. <i>Physica Status Solidi A</i> , 2003, 195, 238-242.	1.7	3
43	Photoelectric properties of highly excited GaN:Fe epilayers, grown by modulation- and continuous-doping techniques. <i>Journal of Crystal Growth</i> , 2007, 300, 228-232.	0.7	3
44	Carrier dynamics in Fe-doped GaN epilayers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S723-S726.	0.8	3
45	Facet analysis of truncated pyramid semi-polar GaN grown on Si(100) with rare-earth oxide interlayer. <i>Journal of Applied Physics</i> , 2016, 120, 105301.	1.1	3
46	Temperature and spatial dependence of carrier lifetime and luminescence intensity in Ge <sub>0.95</sub> Sn <sub>0.05</sub> layer. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2021, 270, 115204.	1.7	3
47	Heterodyne detection scheme for light-induced transient grating experiment. <i>Optics Communications</i> , 2008, 281, 6061-6064.	1.0	2
48	Advantages of the time-resolved four-wave mixing technique for studies of non-equilibrium carrier dynamics in bulk semiconductors and structures. <i>Optical Materials</i> , 2008, 30, 780-782.	1.7	2
49	High-excitation luminescence properties of m-plane GaN grown on LiAlO <sub>2</sub> substrates. <i>Journal of Crystal Growth</i> , 2011, 329, 33-38.	0.7	2
50	Highly efficient nanocrystalline Cs <sub>x</sub> MA <sub>1-x</sub> PbBr <sub>x</sub> perovskite layers for white light generation. <i>Nanotechnology</i> , 2019, 30, 345702.	1.3	2
51	Nonlinear Optical Techniques for Characterization of Wide Bandgap Semiconductor Electronic Properties: III-nitrides, SiC, and Diamonds. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1396, .	0.1	1
52	Peculiarities of photoluminescence efficiency dependence on excitation intensity in GaN/Al <sub>2</sub> O <sub>3</sub> epilayers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 511-514.	0.8	1
53	Relationships Between Strain and Recombination in Intermediate Growth Stages of GaN. <i>Journal of Electronic Materials</i> , 2014, 43, 2667-2675.	1.0	1
54	Improvement of luminescence properties of InN by optimization of multi-step deposition on sapphire. <i>Thin Solid Films</i> , 2019, 680, 89-93.	0.8	1

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55	The Crystalline Structure of Thin Bismuth Layers Grown on Silicon (111) Substrates. <i>Materials</i> , 2022, 15, 4847.	1.3	1
56	Defect study of GaN based LED structure by electron beam induced current. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 734-737.	0.8	0
57	The importance of nucleation layer for the GaN N-face purity on the annealed Al <sub>2</sub> O <sub>3</sub> layers deposited by atomic layer deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2022, 284, 115850.	1.7	0